

# Wide-band Induction Acceleration in the KEK Digital Accelerator

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<sup>4</sup>The Graduate University for advanced Studies,

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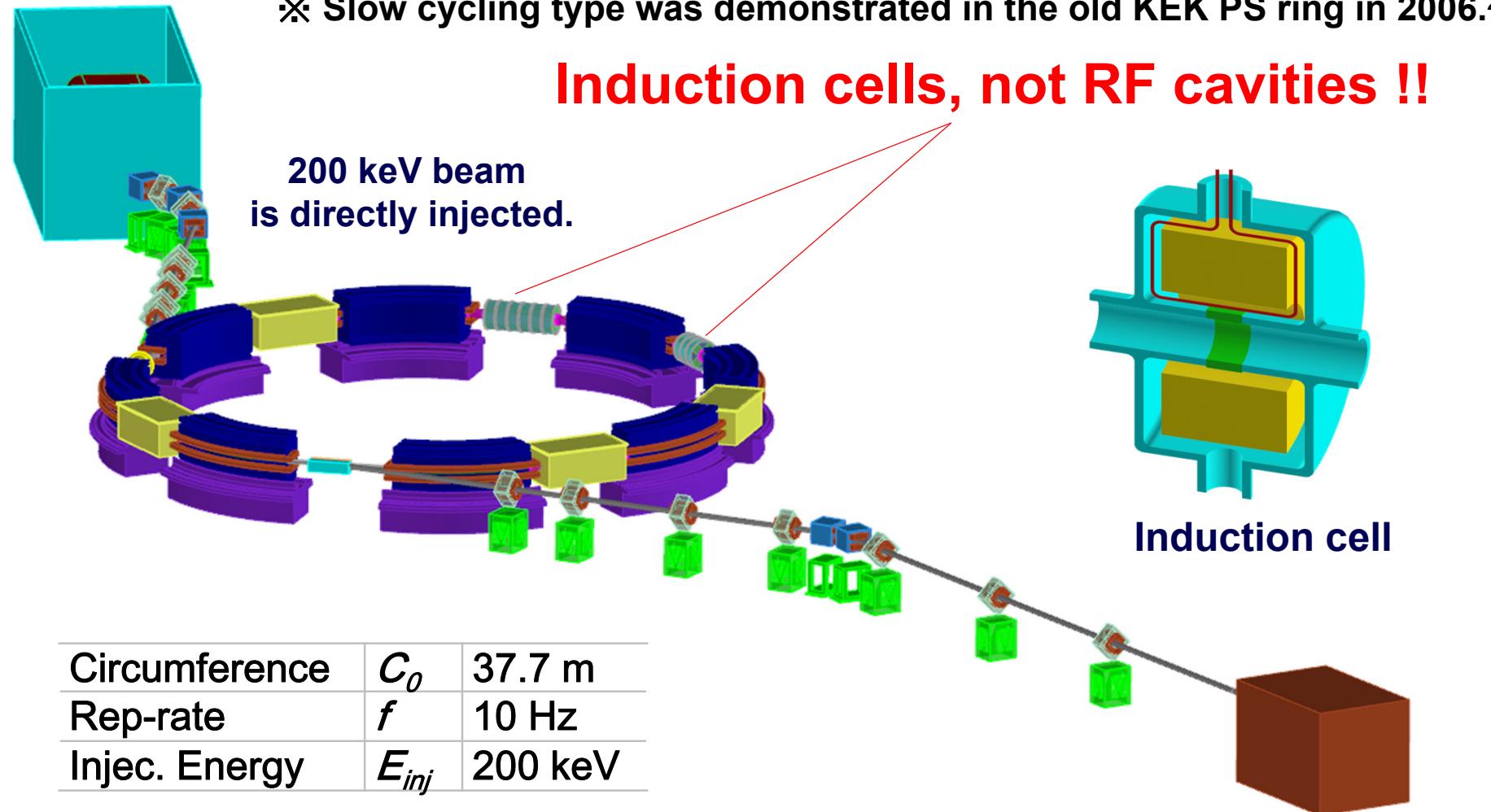
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- ◆ What is induction synchrotron ?
- ◆ Three features of induction synchrotron
- ◆ Outline of KEK digital accelerator
- ◆ Wide band acceleration
- ◆ Novel beam handling
- ◆ Conclusion

# What is Induction synchrotron ?

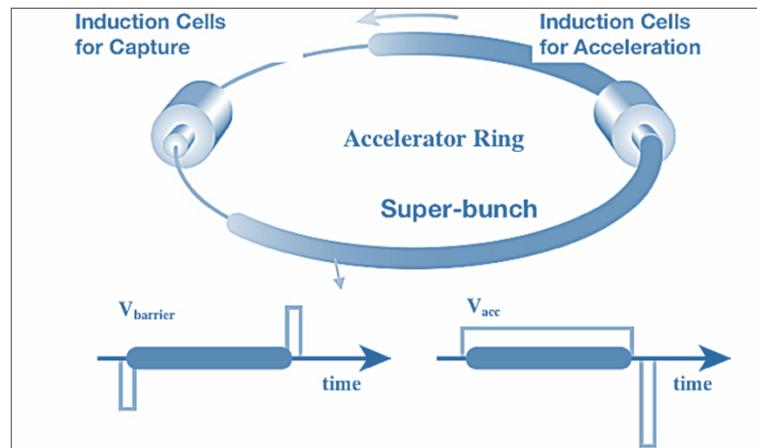
KEK digital accelerator (Wide-band fast cycling induction synchrotron)<sup>1)</sup>

※ Slow cycling type was demonstrated in the old KEK PS ring in 2006.<sup>2)</sup>

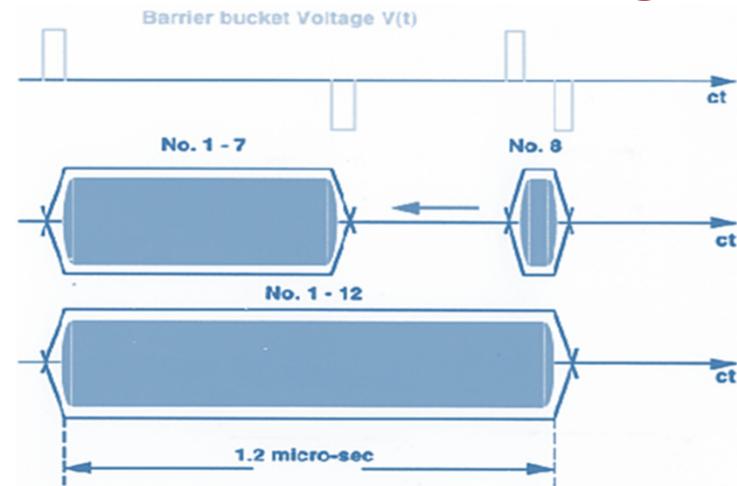


# Three notable features of Induction synchrotron

## Super-bunch acceleration<sup>1)</sup>



## Novel beam handling



## Wide-band acceleration<sup>2)</sup>

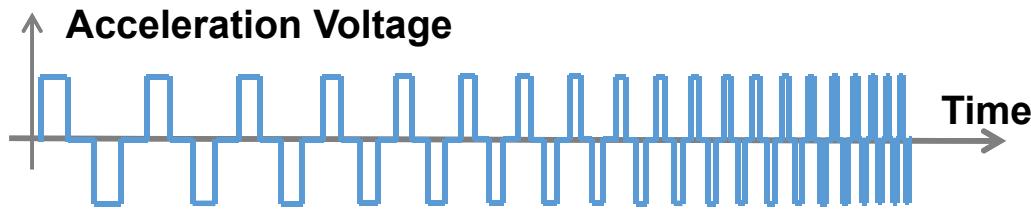
### Advantages

Rev. frequency: 0 ~ a few MHz

Wide variety of ion species can be provided in a broad energy range.

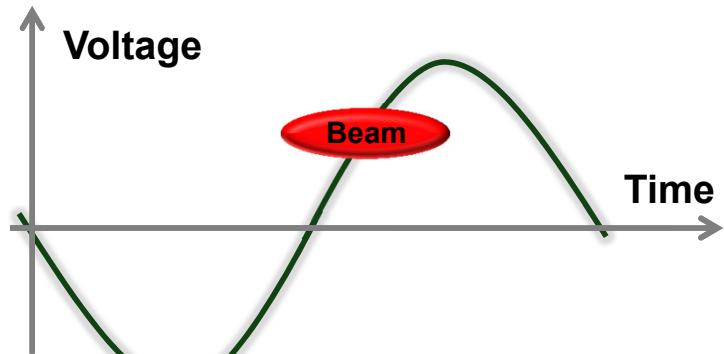
### Disadvantages

- Space charge limit & residual gas interactions in low energy region
- In small ring (~100 m), max. rev. frequency is limited by semiconductor switching of acc. volt..

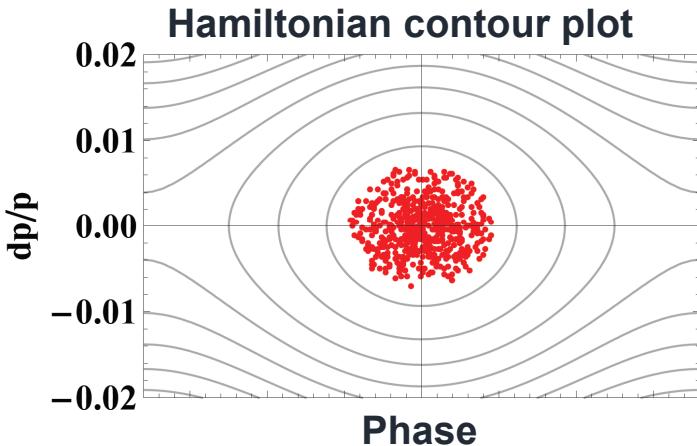


# RF acceleration & Induction synchrotron

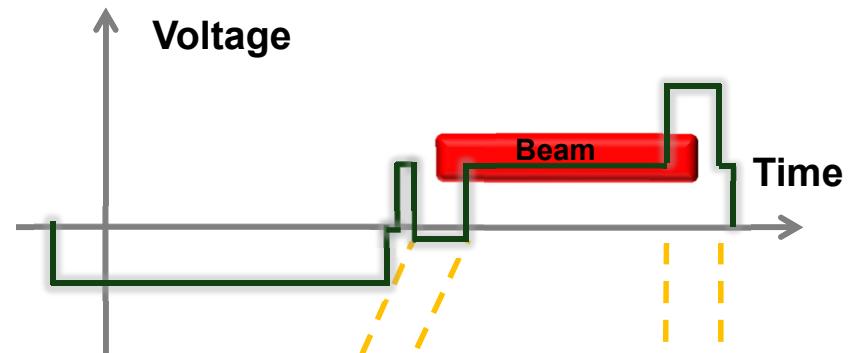
## Conventional RF acceleration



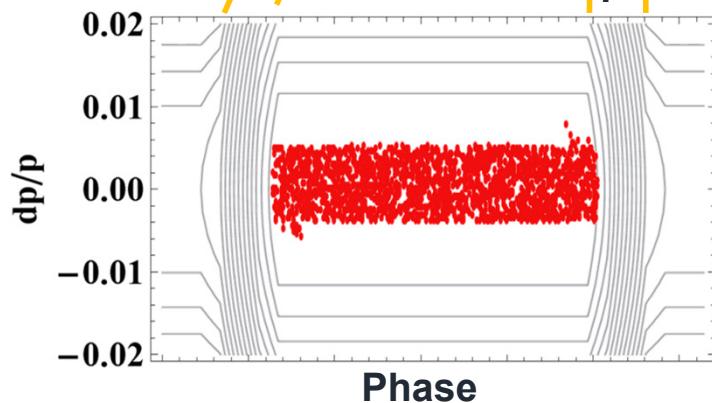
Confinement & Acceleration function are combined.



## Induction acceleration

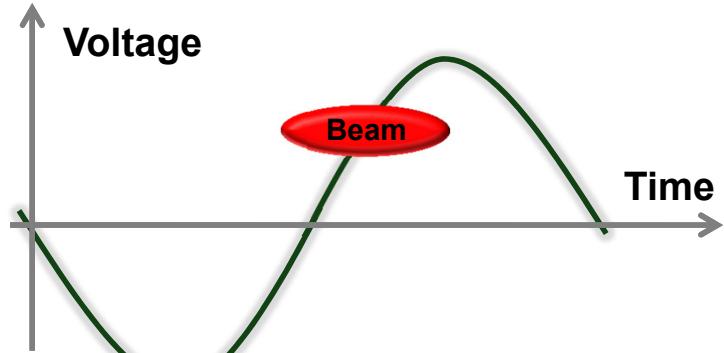


Hamiltonian contour plot

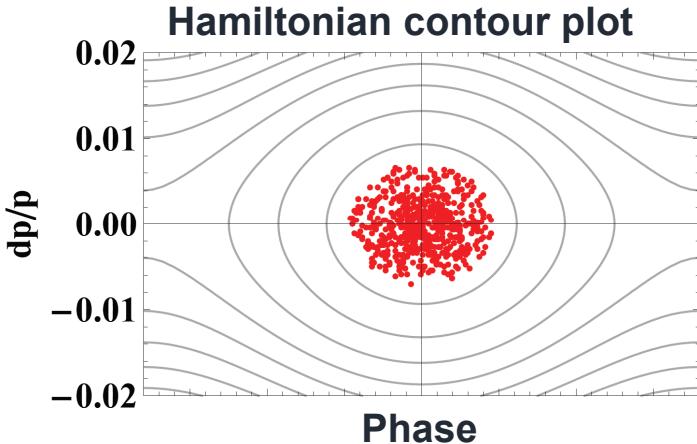


# RF acceleration & Induction synchrotron

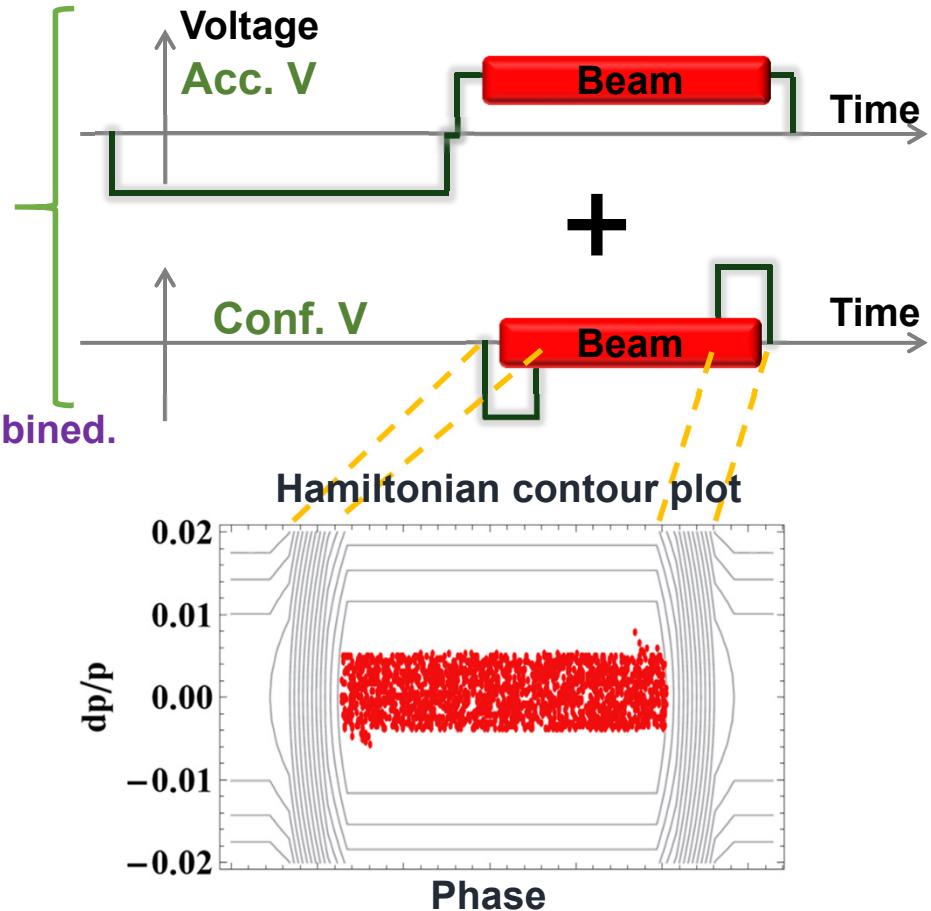
## Conventional RF acceleration



Confinement & Acceleration function are combined.

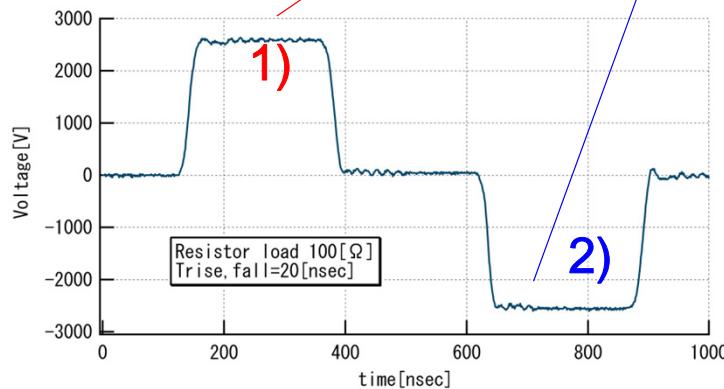
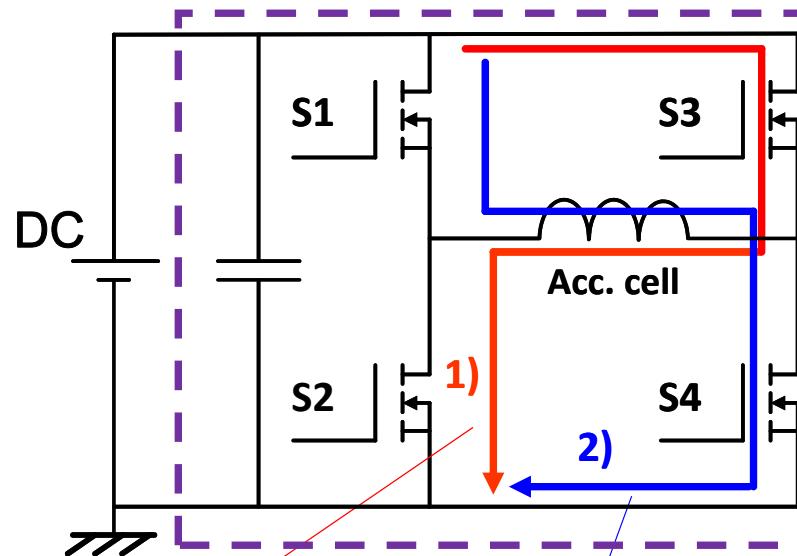


## Induction acceleration

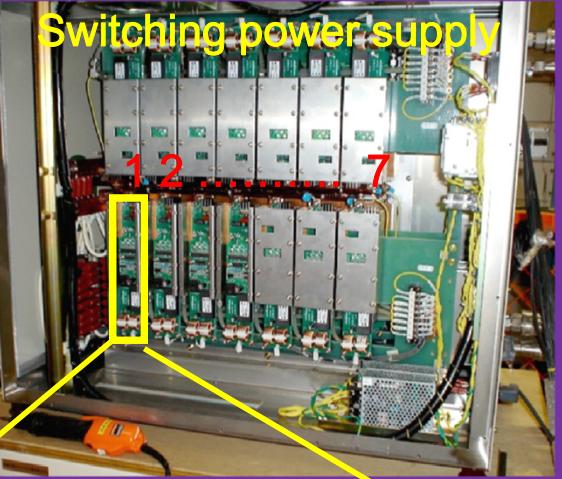


5 Separate function can creates a longer bucket  $\Rightarrow$  mitigating space charge effect.

# Switching Power Supply for Induction cells



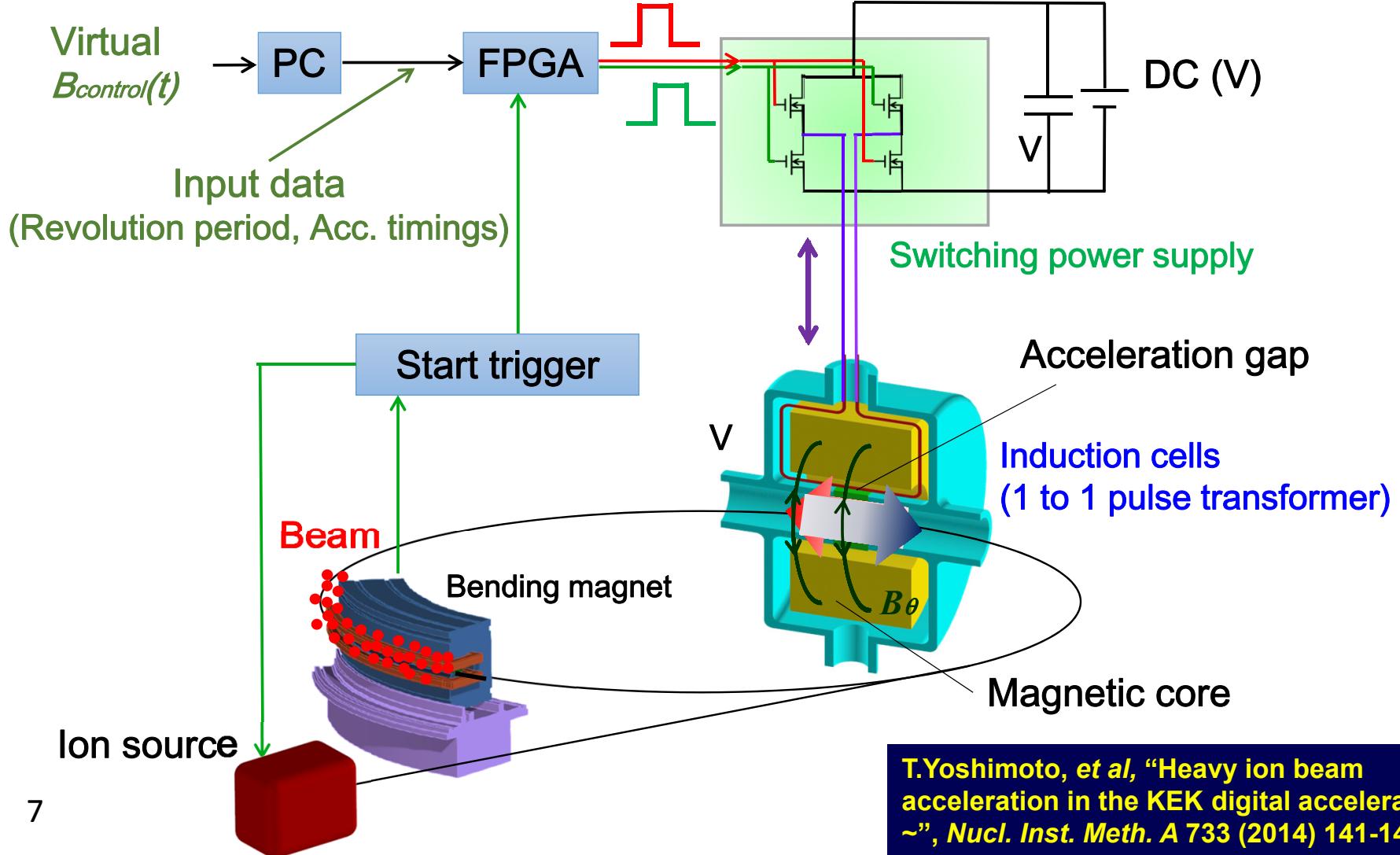
Waveform generated by switching power supply  
(2.5kV, 20A, 1MHz)



Next generation of SPS: K.Okamura, *et al.*, MOPME068 in IPAC'14  
"SiC-JFET Switching Power Supply toward for Induction Ring Accelerators"

# Fully programmed control of KEK digital accelerator

In advance, all information for acceleration timings is load to FPGA.  
Virtual  $B(t)$  decides ideal revolution period and acc. timings.



# How to generate confinement voltages

Reference signals: 12  $\mu$ s  $\rightarrow$  1  $\mu$ s  
 (which generate every ideal rev. period of beam)

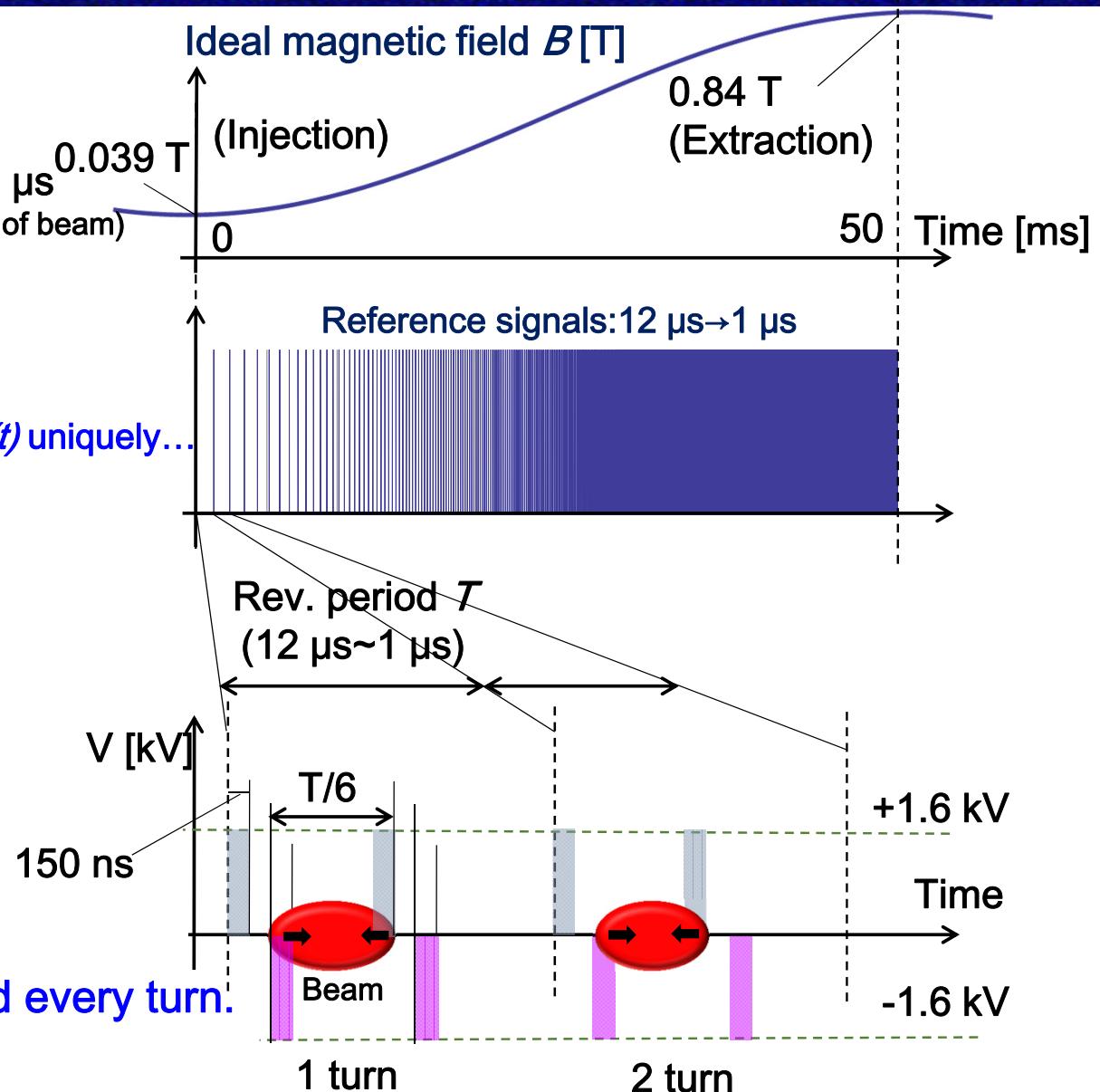
$$T(t) = \frac{C_0}{c} \sqrt{\frac{1+D}{D}}$$

$B(t)$  determines  $T(t)$  uniquely...

$$D = \left\{ \left( \frac{Q}{A} \right) \left( \frac{e\rho}{m_0 c} \right) \right\}^2 B^2$$

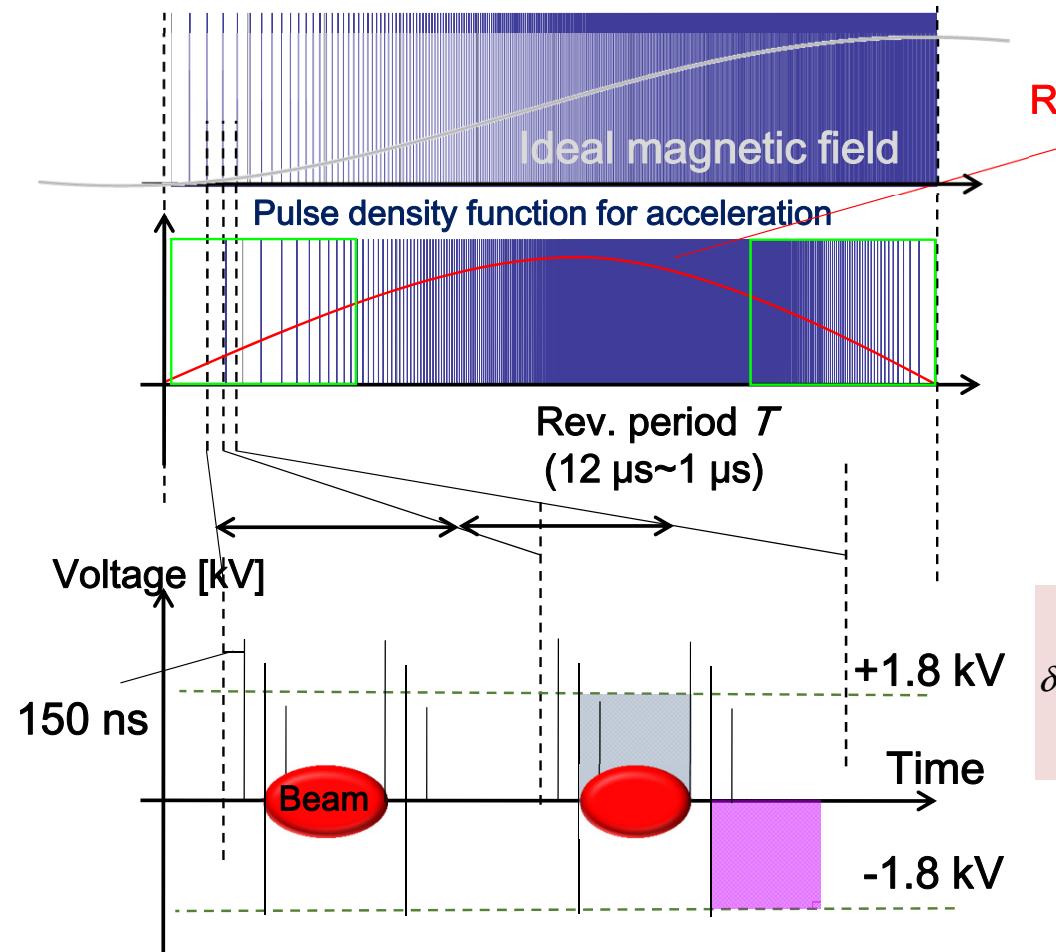
Here,  
 ratio of charge to mass :  $Q/A$   
 charge element :  $e$   
 bending radius:  $\rho$   
 unit mass:  $m_0$   
 ideal magnetic field :  $B(t)$

Conf. voltages are generated every turn.



# How to generate acceleration voltage

Reference signals (signals of ideal rev. period) :  $12 \mu\text{s} \rightarrow 1 \mu\text{s}$



Required acc. voltage per turn  $V(t)$ :

$$V(t) = \rho C_0 \frac{dB(t)}{dt}$$

$\rho$  : bending radius  
 $C_0$  : circumference  
 $B(t)$ : ideal magnetic field

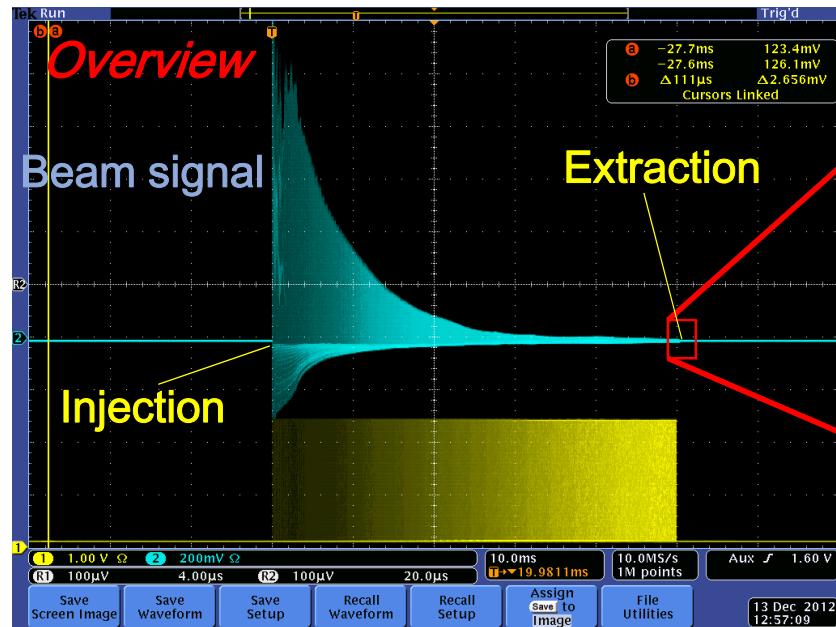
$$\delta(N+1) = \begin{cases} 1 & \cdots \left( \sum_{n=1}^{N+1} V(n) - V_0 \sum_{n=1}^N \delta(n) \right) > V_0 \\ 0 & \cdots \left( \sum_{n=1}^{N+1} V(n) - V_0 \sum_{n=1}^N \delta(n) \right) < V_0 \end{cases}$$

$V_0$ : constant induction acc. voltage  
 $\delta(n)$ : acc. density table  
 $N$ : turn number

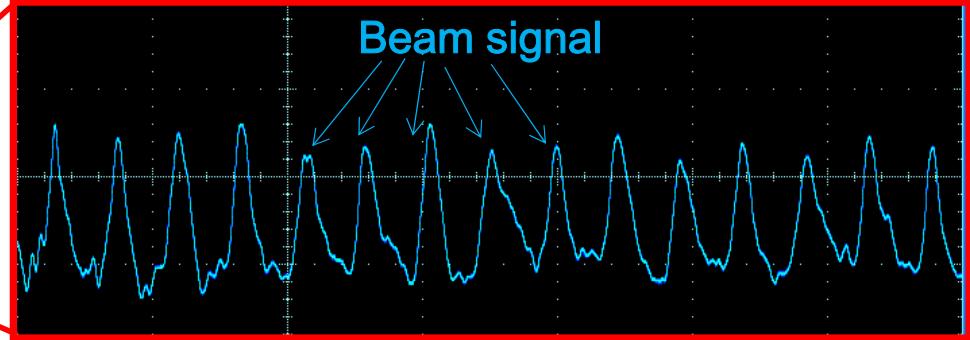
Induction acc. voltages are generated discretely in order to give required acc. voltage spuriously.

→ Pulse density control

# Result of beam acceleration



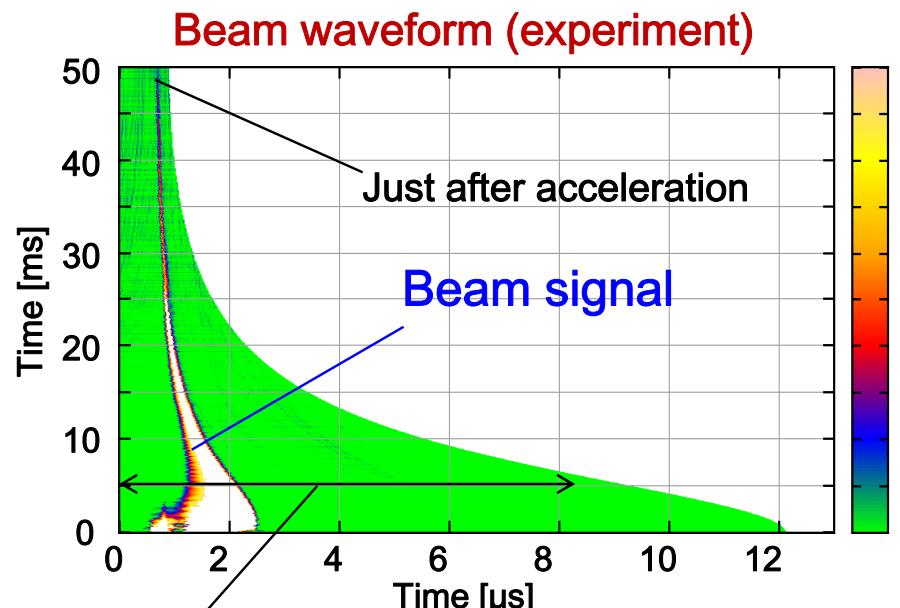
*Zoom-up view (End of acceleration)*



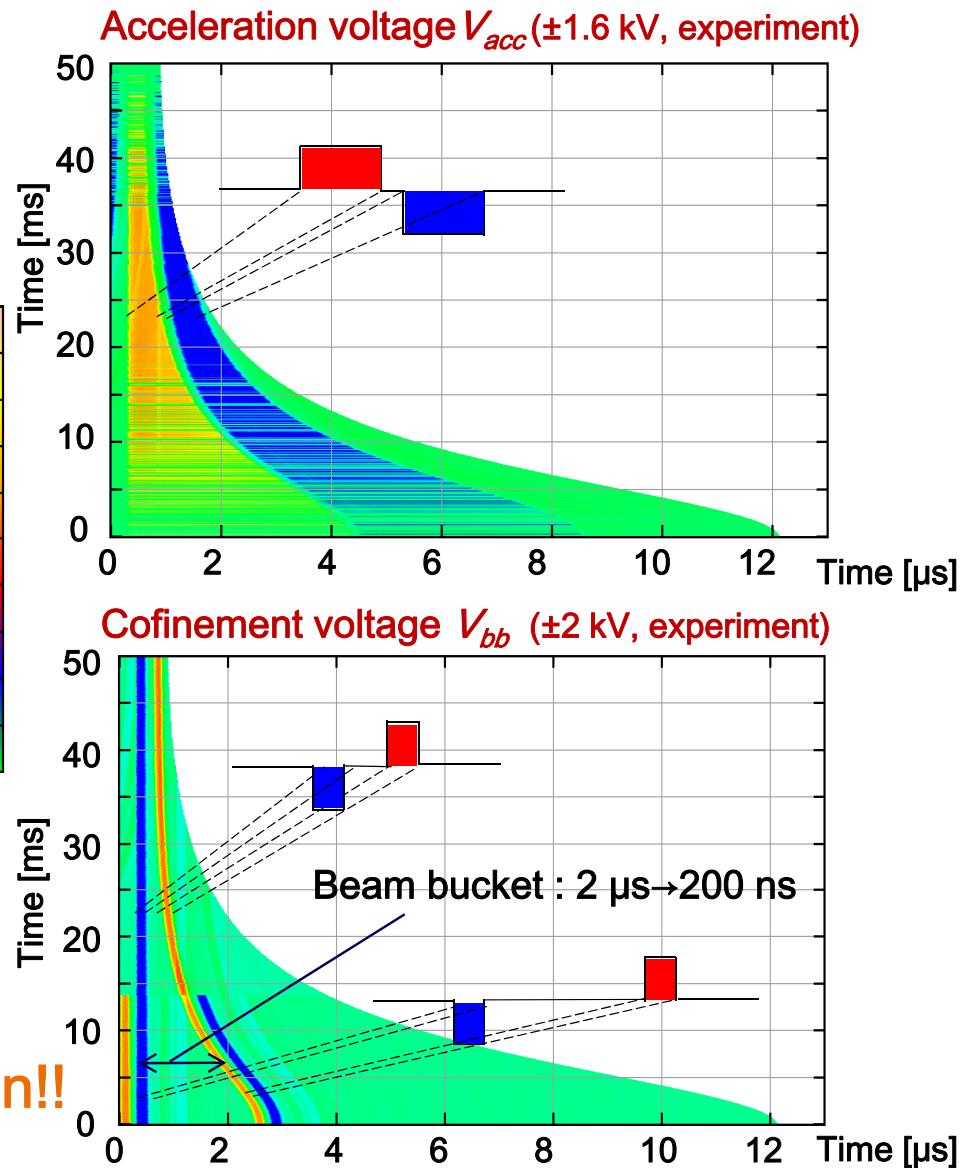
## Beam and machine parameters:

Bending magnetic flux density	0.039 → 0.51 [T]
Mass to charge ratio A/Q	4/1
Energy	0.05→8 [MeV/u]
Injection current	~100 $\mu$ A

# Wide-band acceleration (experiment)



Rev. period:  $12 \mu\text{s} \rightarrow 1 \mu\text{s} !!$



Success of wide-band acceleration!!

# Beam survival & discussion

**Beam survival: ~ 10%**

## Reasons

- **Vacuum ( $\sim 10^{-6}$  Pa)**

Strong interaction with residual gas in low energy (200 keV ~)

- **Non-zero dispersion optics (D = 1.4 m at Induction cell region )**

Unfortunately, present optics was designed for the PS booster ring 40 years ago.

- **Discrete acceleration**

In our case, acc. voltages are constant because of fixed output of DC power supply.  
Therefore we do not generate acc. voltage every turn.

### *Solution:*

DC power supply with time varying output voltage  
may be ideal to meet required acceleration voltage demand.

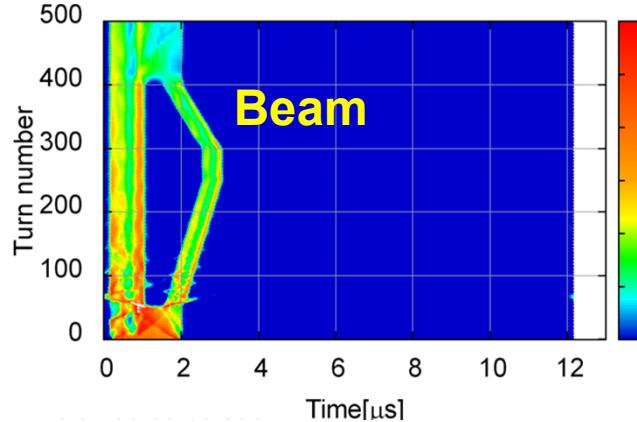
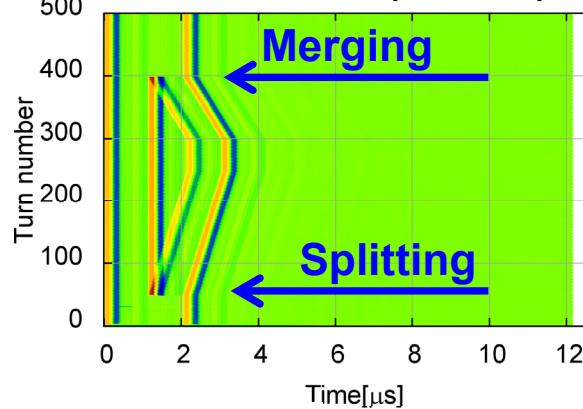
**These three reasons are not issues  
for brand-new future induction synchrotrons.**

# Novel beam handling (Experiment, E = 200 keV, A/Q = 4)

※ preliminary experiment

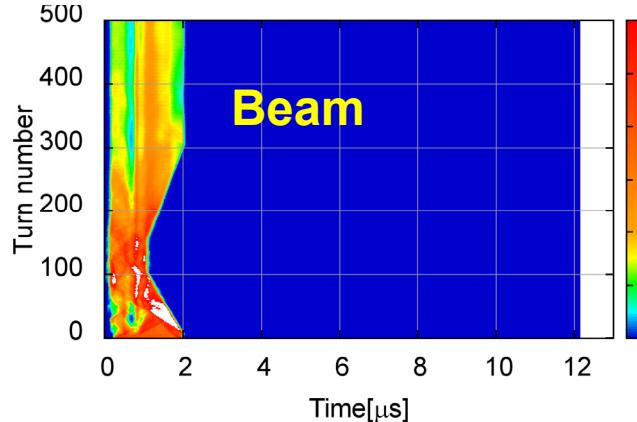
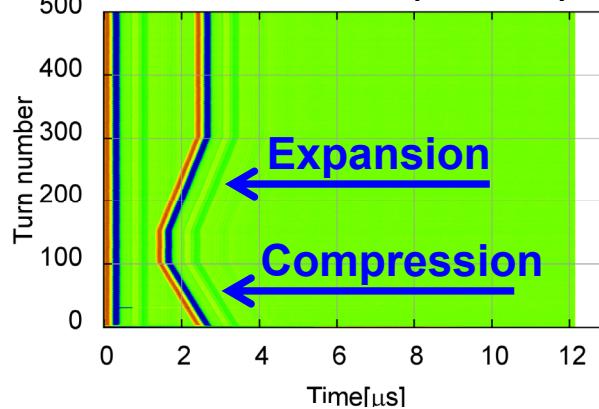
## Splitting & Merging

Beam bucket ( $\pm 1.5$  kV)



## Compression & Expansion

Beam bucket ( $\pm 1.5$  kV)



Combination of these techniques makes various operations.

Ex. 1: Separated beams can be provided to different lines at different energies.

Ex. 2: It is easy to stack bunches at injection.

# Conclusion

We have demonstrated:

- **wide-band acceleration** (Rev.  $f$  : 82 kHz ~ 1 MHz)  
A wide variety of ion species can be provided in a broad energy range for various applications, where high intensity is not required.  
**## There is space charge limit in low energy !!**
- **beam handling** techniques with induction synchrotron.  
Various useful operations are expected soon.

*Future works ...*

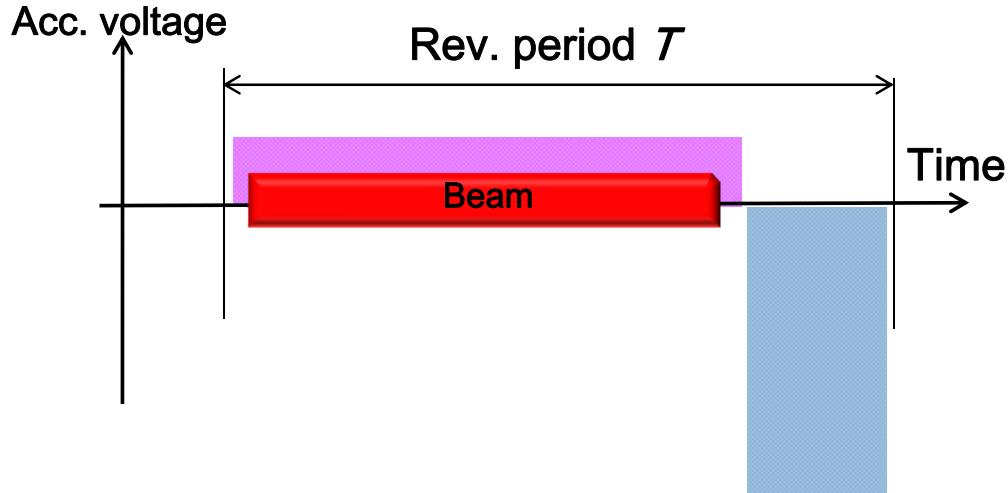
We try to establish the super bunch (very long beam) acceleration.

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**Thank you for attention !!**

# Preparatory Slides

# Super bunch (very long beam) acceleration



## Method 1: Half Bridge SPS

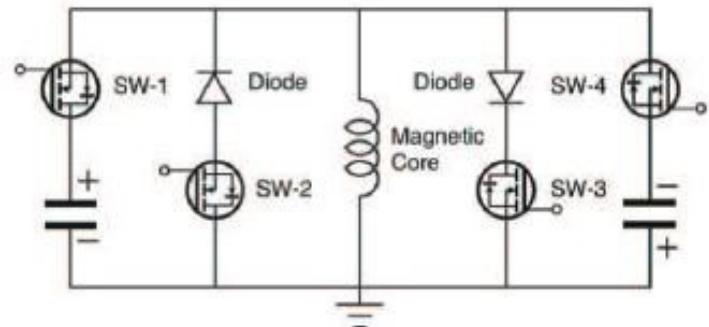
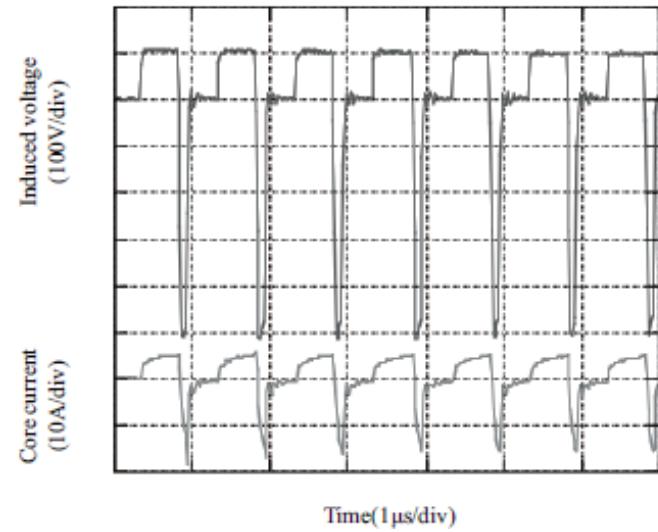
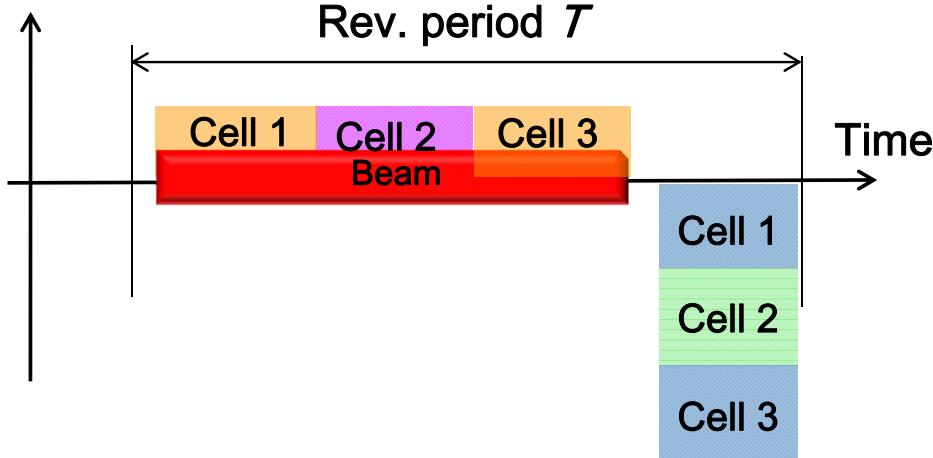


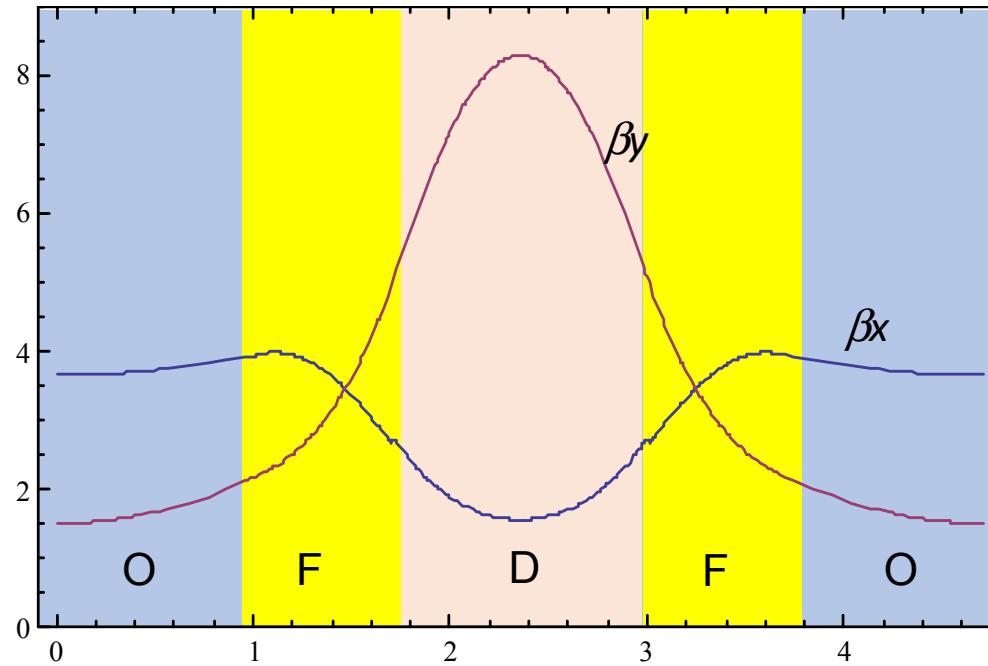
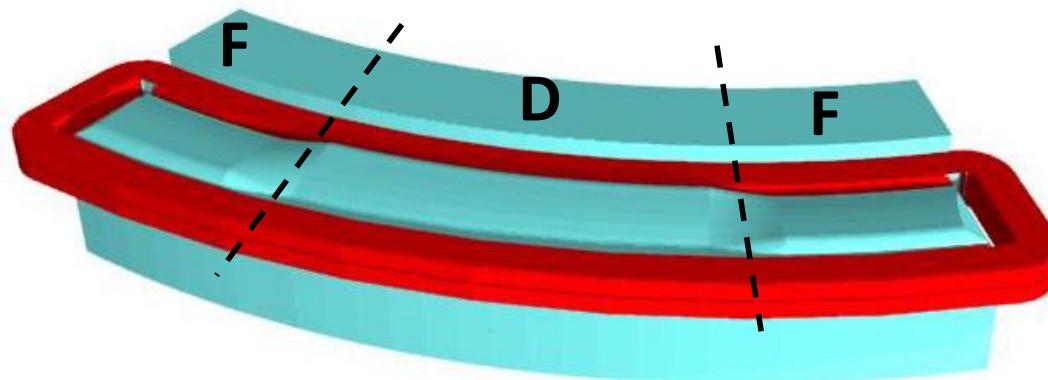
Fig. 11.16. Half bridge modulator.

## Method 2: combined acceleration pulse



(experimental demonstration  
by Dr. Watanabe of Tokyo Tech.)

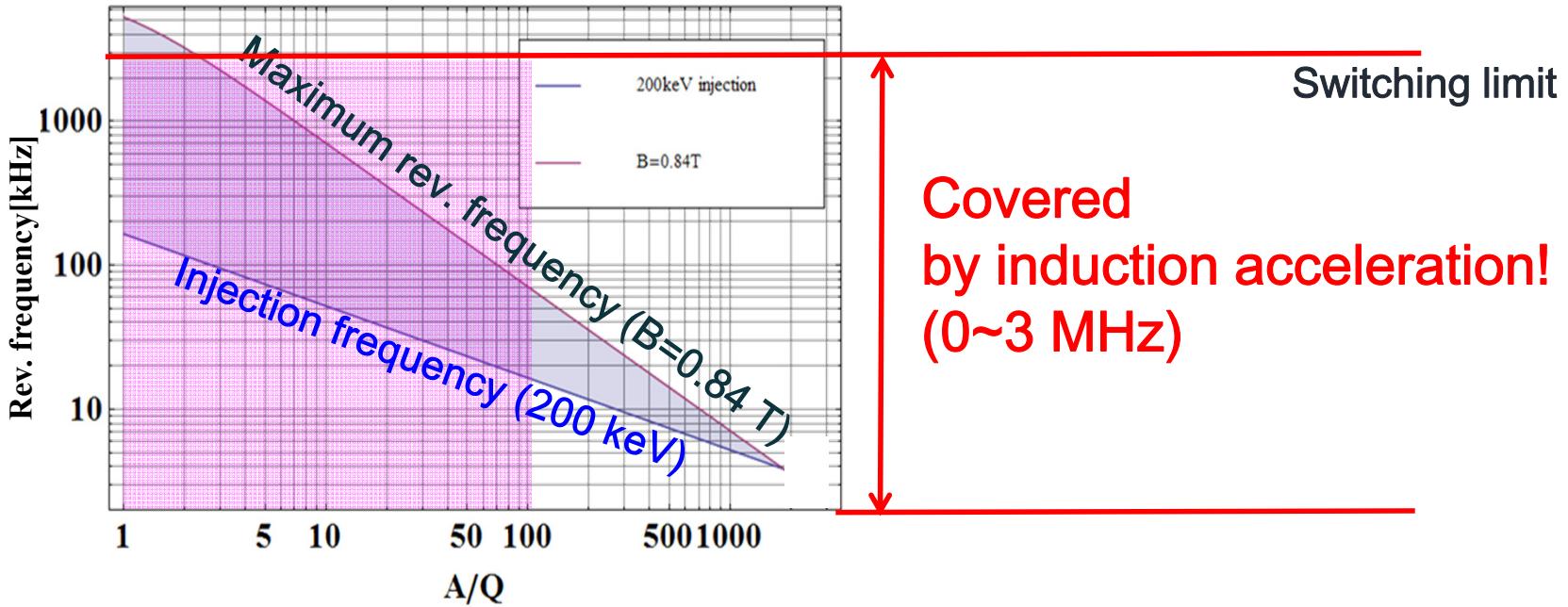
# The ring lattice in the KEK digital accelerator



# Which ion species can be accelerated ?

- ◆ Mass-to-charge ratio of many ions are  $1\sim 100$ .

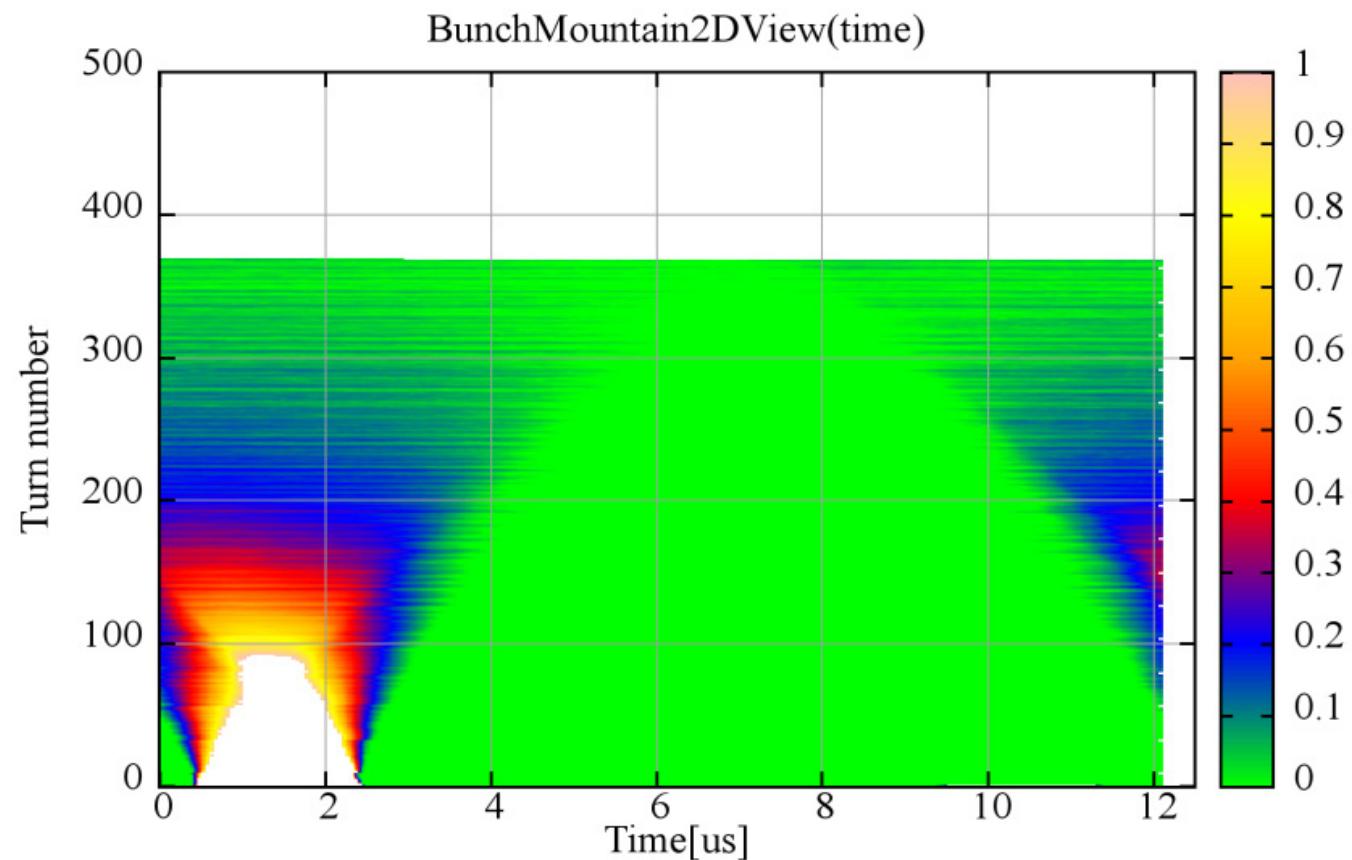
→ Most ions species with any charge state can be directly accelerated.



- ◆ Semiconductor switching capability of induction system limits maximum revolution frequency.

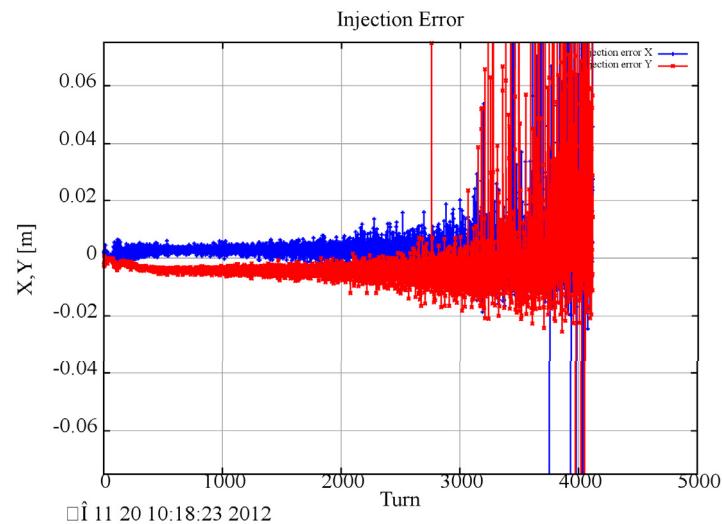
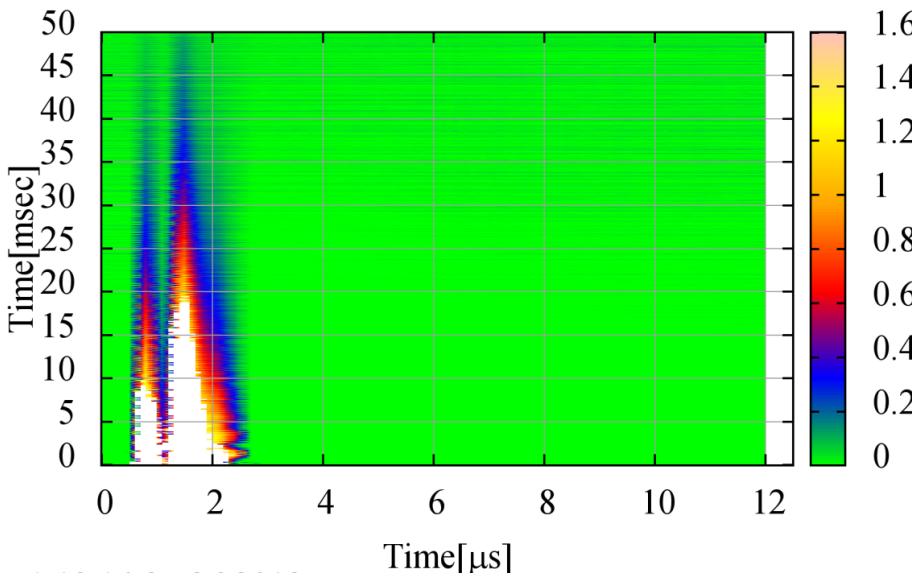
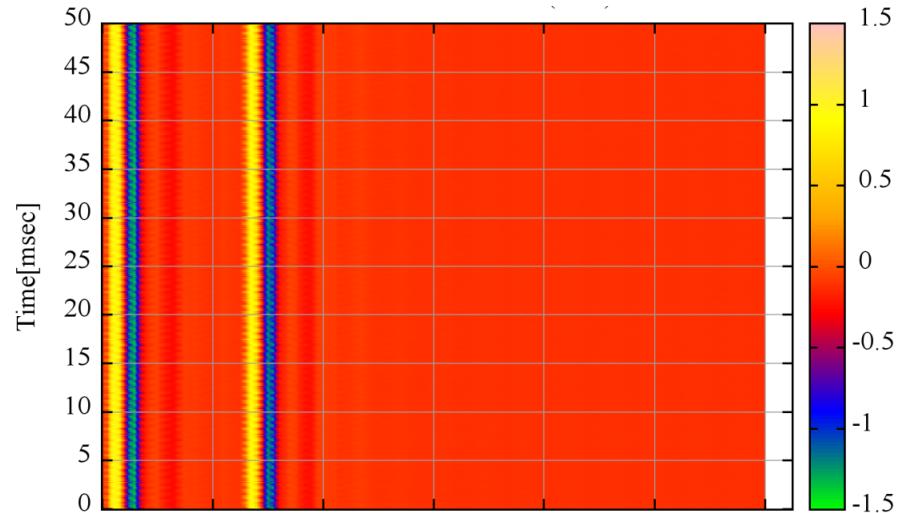
→ In principle, large scale ring can eliminate this problem.

# Free running (200keV A/Q = 4)

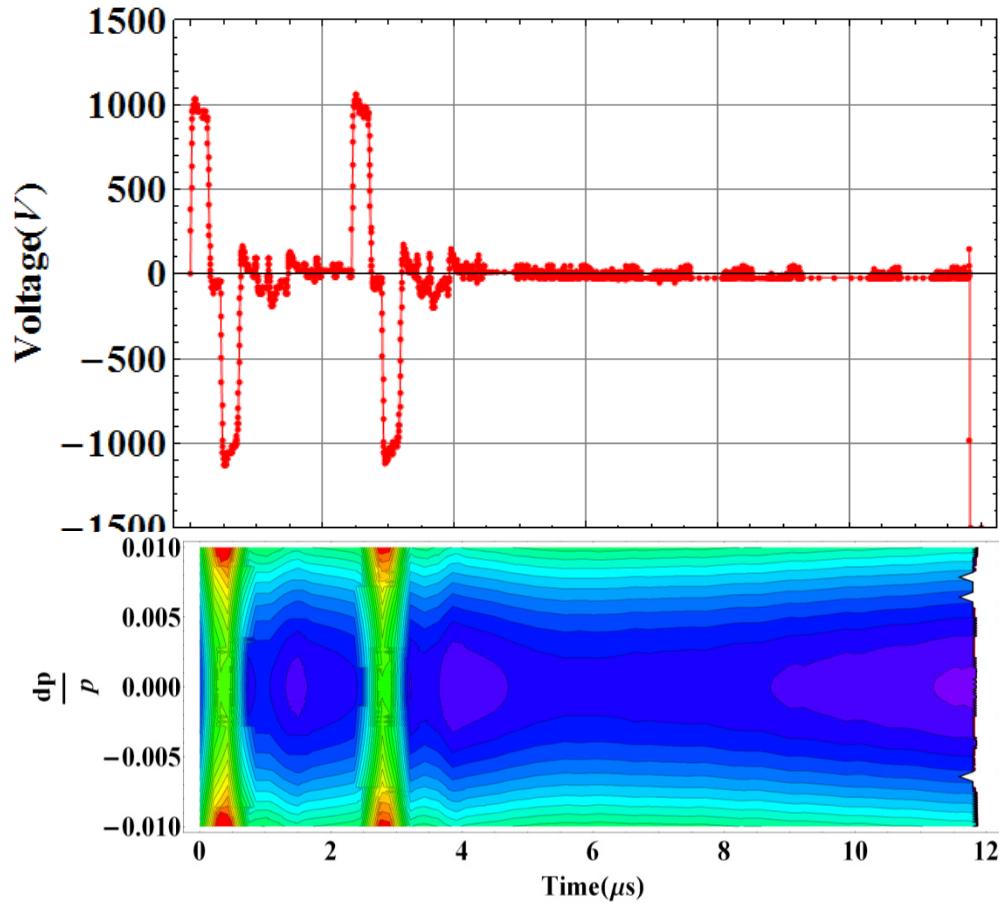


□ 11 13 15:16:09 2012

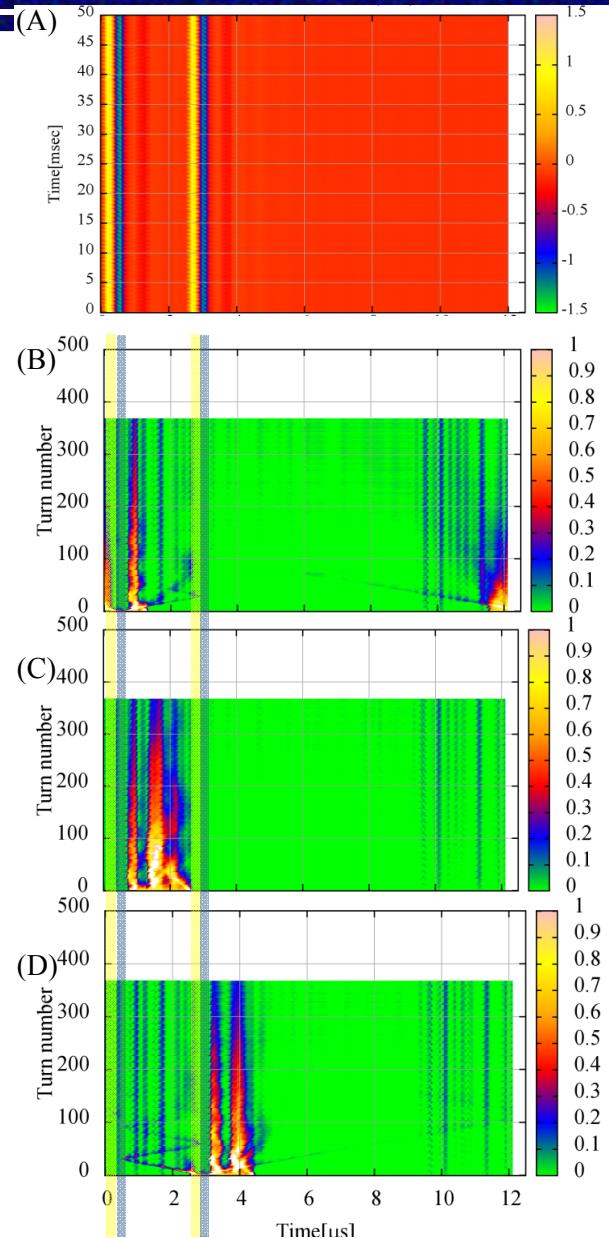
# The Optimization of the barrier bucket position



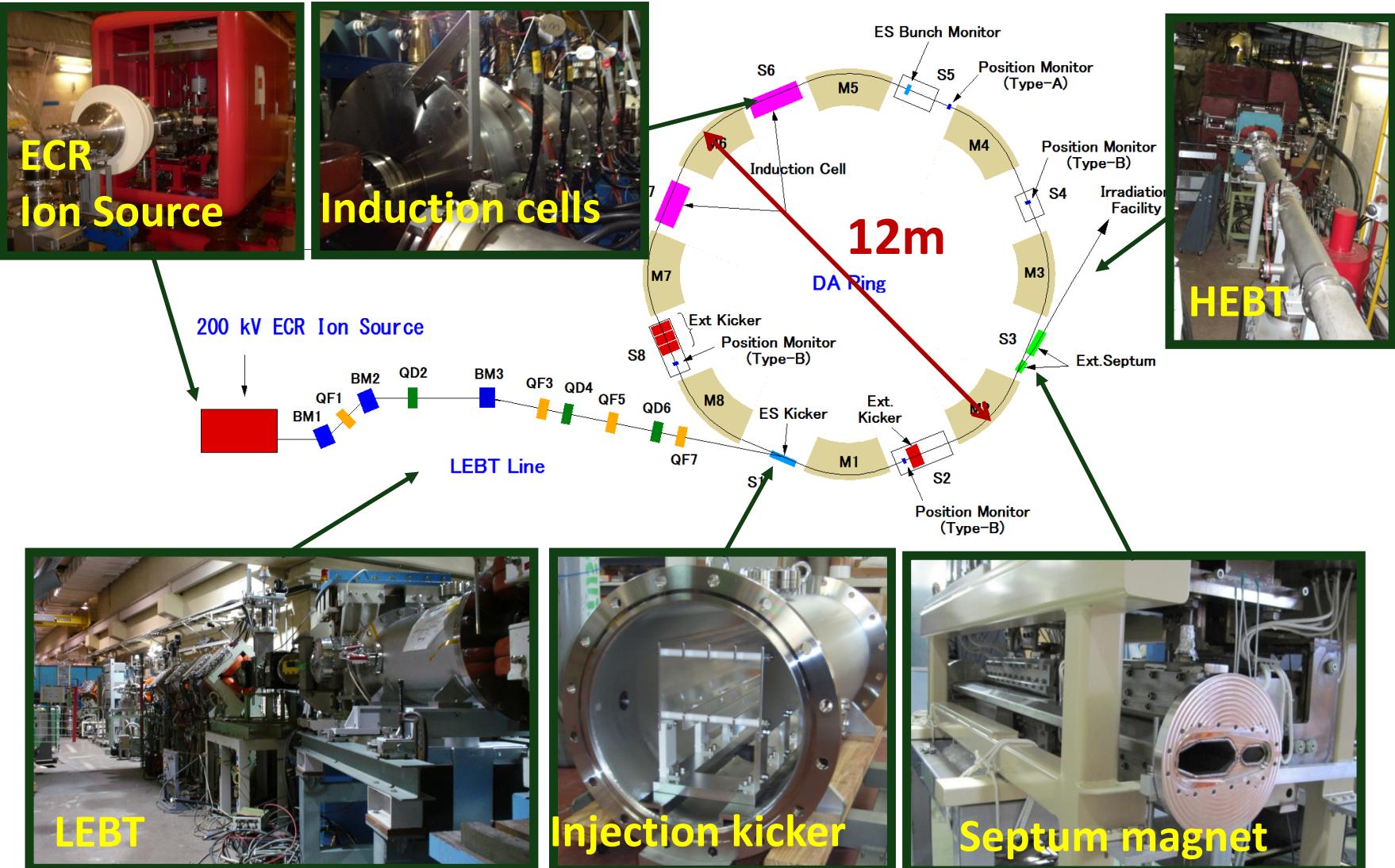
# The Optimization of the barrier bucket position



$$H\left(\frac{dp}{p}, t\right) = \frac{\eta E_s \beta_s^2}{2} \left(\frac{dp}{p_s}\right)^2 + \frac{Z}{h \cdot T} \int_0^t V(t') dt'$$

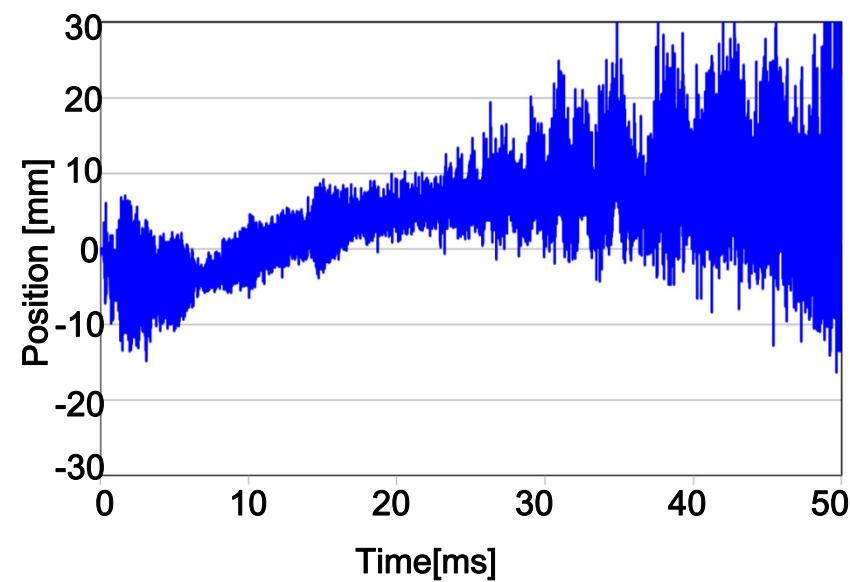


# The Overview of KEK digital accelerator

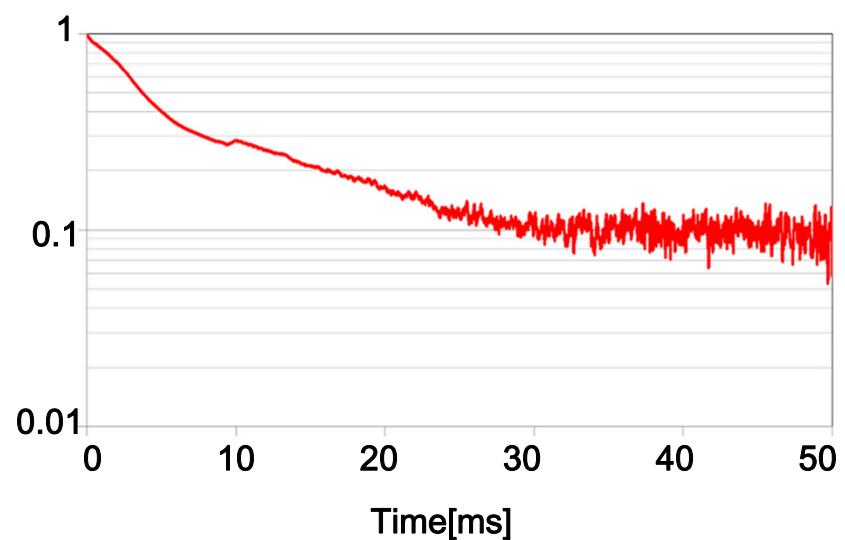


# ビーム加速の解析結果 1

Horizontal beam position

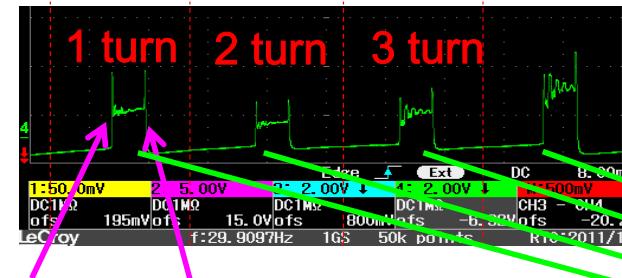


Beam survival: ~10%



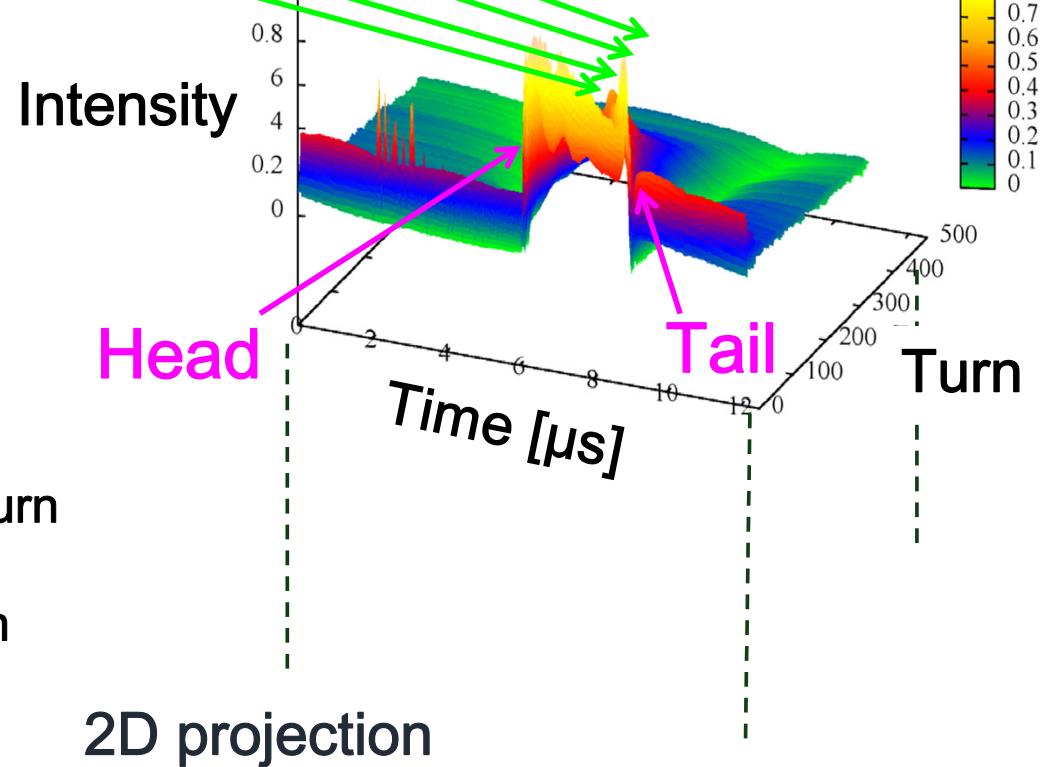
# How to make mountain view

## Monitor signal:



Head Tail

## Mountain view:



## Process:

1. Slicing oscilloscope view every ideal period
2. Arranging each graph in turn
3. Making 2D projection from the combined 3D graph

# Adapting fully predictive control

It is difficult to construct feedback control because of the low S/N ratio of beam signal at present condition.

Method:

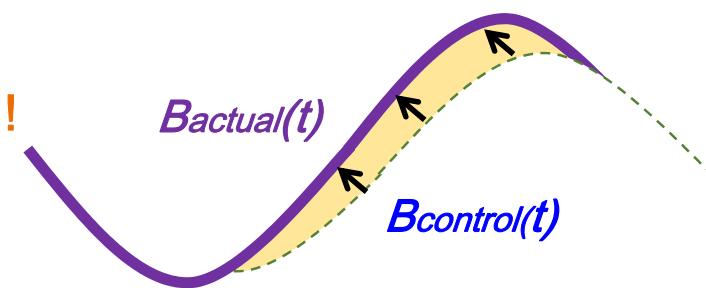


1. We set ideal magnetic flux density  $B_{control}(t)$ , calculate all required ideal periods and acceleration timings and write them in FPGA in advance.
2. We can modify ideal magnetic field  $B_{control}(t)$  to correspond actual magnetic field  $B_{actual}(t)$  from beam motion.

Actual magnetic field    Ideal magnetic field

$$B_{actual}(t) = B_{control}(t) \Leftrightarrow \begin{cases} B_{actual\_max} = B_{control\_max} & (\text{Max. B}) \\ B_{actual\_min} = B_{control\_min} & (\text{Min. B}) \\ \delta = 0 & (\text{Phase difference}) \end{cases}$$

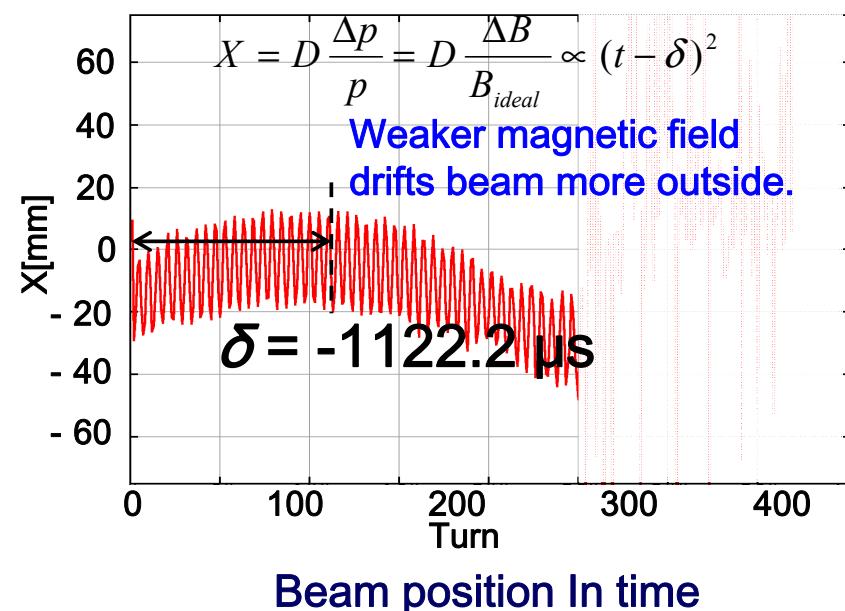
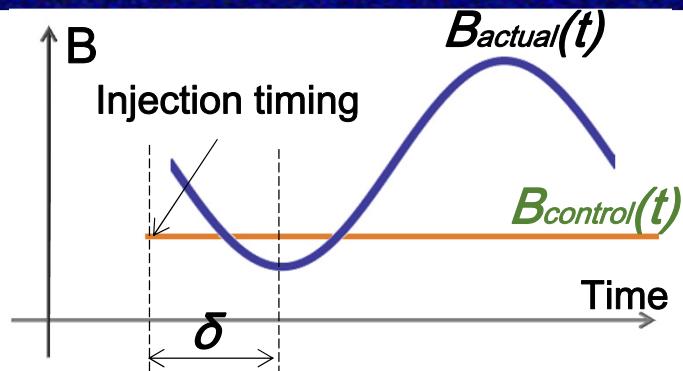
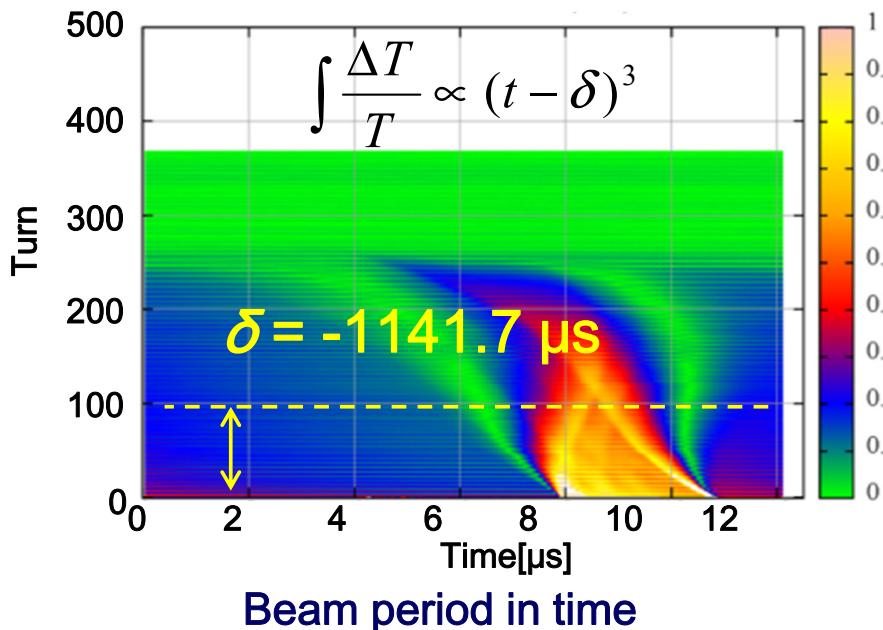
It is essential for beam acceleration  
that Both magnetic fields are corresponded!!



# Minimization of phase difference $\delta$ between ideal and actual magnetic field (Free running)

**Method:**

1. Injecting beam quite before actual injection timing arbitrary
2. Observing horizontal beam position and beam period in time

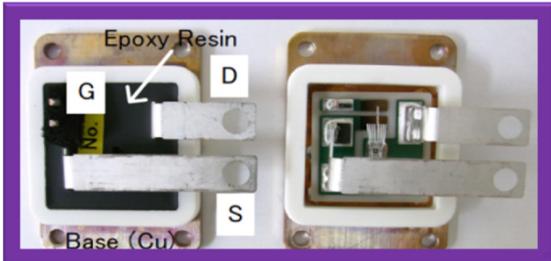


Using this method, we can minimize phase difference  $\delta$   
with the precision under one rev. period.

# Development of Switching Power Supply (SPS)

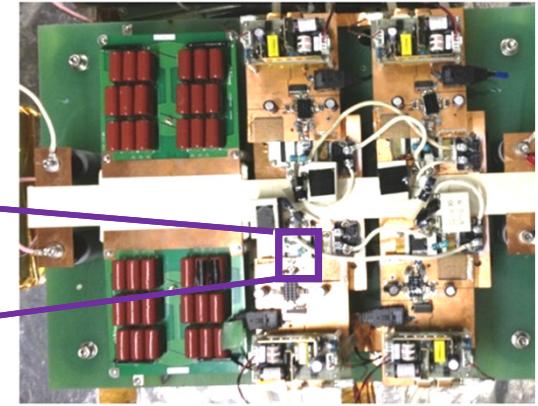


1<sup>st</sup> Gen.: 0.7 kV Si-MOSFET board

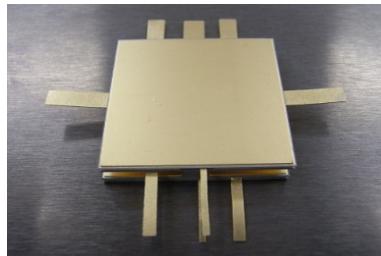


2<sup>nd</sup> Gen.: 1.2 kV SiC-JFET (custom package)

1<sup>st</sup> GEN. SPS(7 MOSFETs in series)



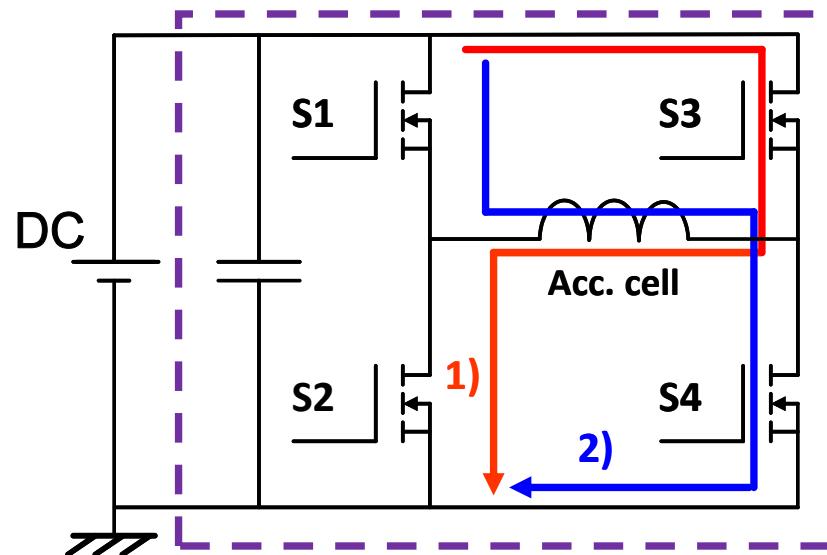
2<sup>nd</sup> Gen.: SPS



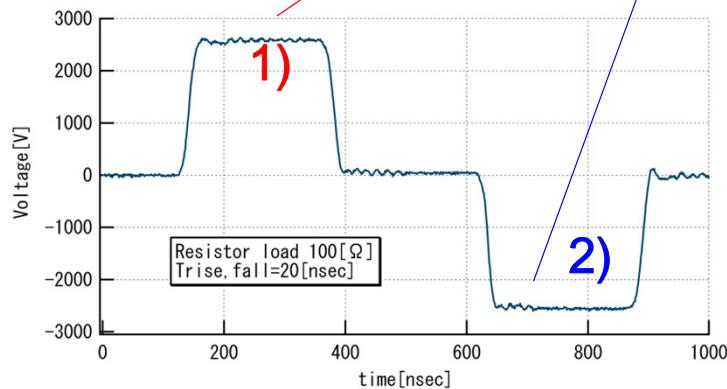
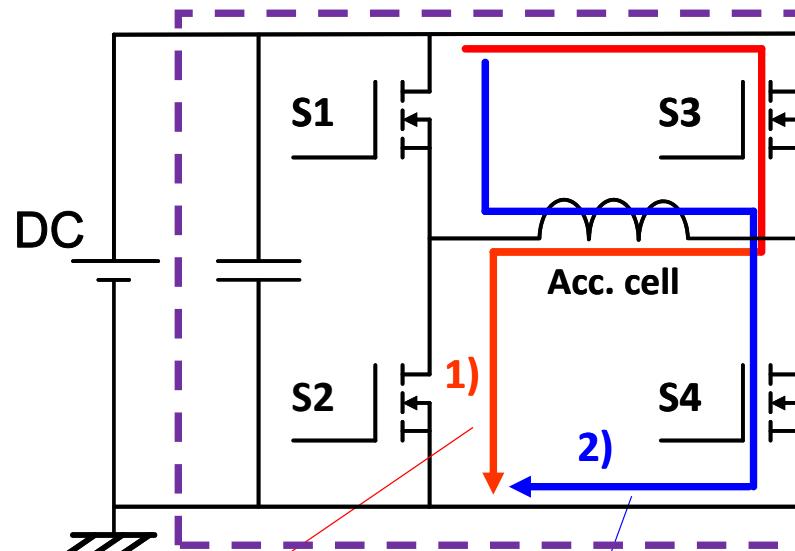
3<sup>rd</sup> Gen. 2.4 kV (custom package)

K.Okamura, et al , MOPME068 in IPAC'14

4<sup>th</sup> Gen. :3.3 kV SiC-MOSFET in 2015

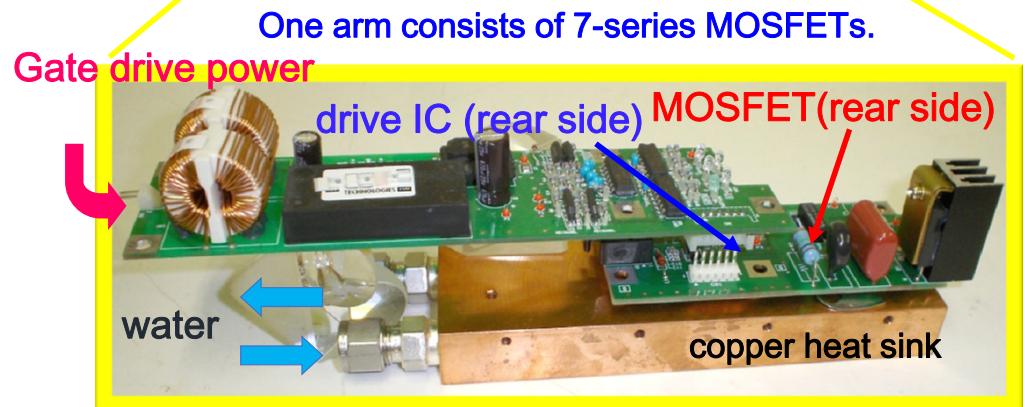
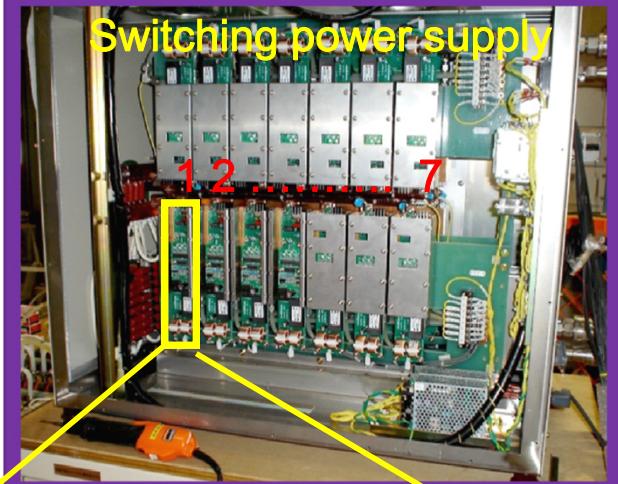


# Switching Power Supply for Induction cells



Waveform generated by switching power supply  
(2.5kV, 20A, 1MHz)

Switching power supply



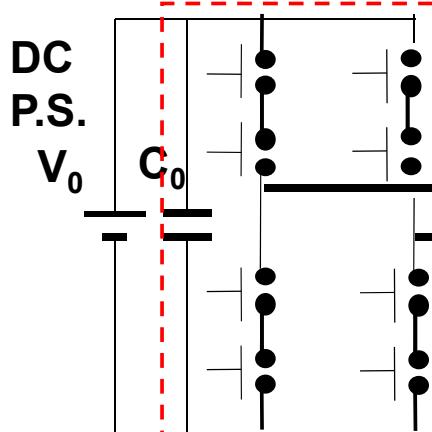
Next generation of SPS: K.Okamura, *et al.*, MOPME068 in IPAC'14  
"SiC-JFET Switching Power Supply toward for Induction Ring Accelerators"

## Possible Questions

- Applications of heavy ions delivered from the KEK-DA?
- Applications as an accelerator technology?
- How is wake fields serious in an induction synchrotron?  
(What happens in high intensity drivers based  
on induction acceleration?)
- How is noise problem overcome?  
(Induction synchrotron is a fully pulse machine.)

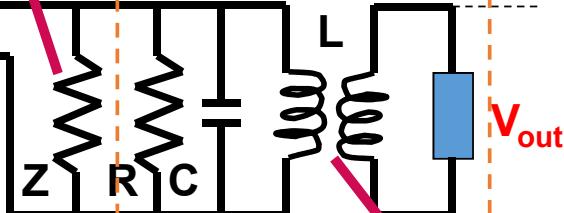
# KEK Evolutional Induction Acceleration System

## Switching power supply



## Matching register

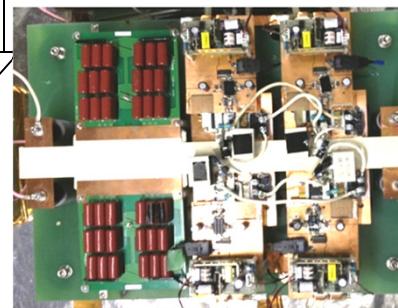
### Induction cell



## Primary terminal



Switchingarm S1  
(7 MOSFETs in series)



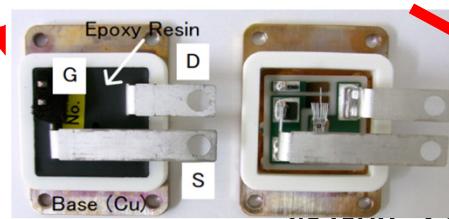
4<sup>th</sup> Gen.  
3.3 kV SiC-MOSFET  
in 2015

2<sup>nd</sup> Gen.  
SPS and  
1.2 kV SiC-MOSFET

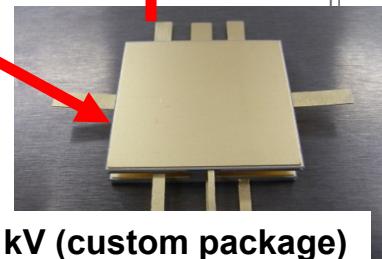
Magnet material  
nanocrystalline  
(custom package)

K.Okamura, et al ,  
MOPME068  
in IPAC'14

1<sup>st</sup> Gen.: 0.7 kV Si-MOSFET board



3<sup>rd</sup> Gen. 2.4 kV (custom package)



Stack of 4 cells  
 $V_{out}=3$  kV/cell